MITSUBISHI ELECTRIC

< C band internally matched power GaAs FET >

MGFC40V5258

5.2 - 5.8 GHz BAND / 10W

DESCRIPTION

The MGFC40V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 – 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation
Internally matched to 50(ohm) system
- High output power
  P1dB=10W (TYP.) @f=5.2 – 5.8GHz
- High power gain
  GLP=10dB (TYP.) @f=5.2 – 5.8GHz
- High power added efficiency
  P.A.E.=32% (TYP.) @f=5.2 – 5.8GHz

APPLICATION

- item 01 : 5.2 – 5.8 GHz band power amplifier
- item 51 : 5.2 – 5.8 GHz band digital radio communication

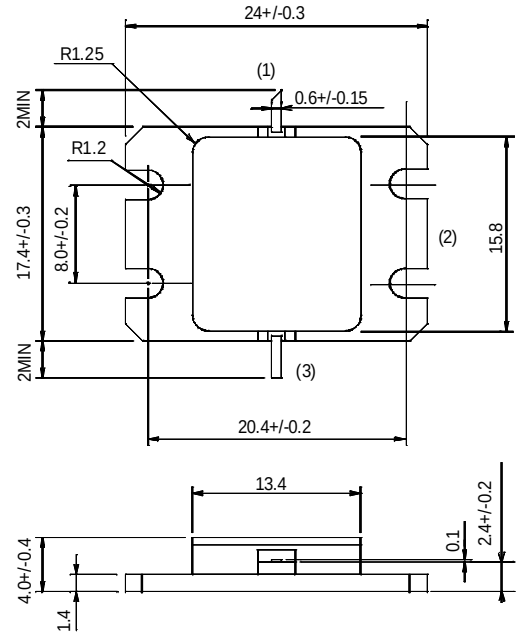
QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=2.4A • RG=50ohm

OUTLINE DRAWING Unit: millimeters (inches)



(1): GATE
(2): SOURCE (FLANGE)
(3): DRAIN

GF-18

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	7.5	A
IGR	Reverse gate current	-20	mA
IGF	Forward gate current	42	mA
PT *1	Total power dissipation	42.8	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

Keep Safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable , but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury , fire or property damage. Remember to give due consideration to safety when making your circuit designs , with appropriate measure such as (I) placement of substitutive , auxiliary circuits , (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	4.5	6	A
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=40mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	39.5	40.5	-	dBm
GLP	Linear Power Gain	f=5.2 – 5.8GHz	8	10	-	dB
ID	Drain current		-	2.4	-	A
P.A.E.	Power added efficiency		-	32	-	%
Rth(ch-c) *3	Thermal resistance		-	-	3.5	°C/W

*2 :item -51 ,2 tone test,Po=29dBm Single Carrier Level ,f=5.0GHz,delta f=10MHz
*3 :Channel-case

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